

IN THE CLAIMS

1. (currently amended): A semiconductor device comprising:

a semiconductor chip having an electrode pad electrically connected to an integrated circuit and a conducting part electrically connected to the electrode pad;
an insulating material formed on a side of the semiconductor chip; and
a conductive pattern to extend from a top of a front side of the insulating material to the conducting part of the semiconductor chip; wherein

the conductive pattern has a first width adjacent to the conducting part, and a second width adjacent to the conductive pattern, the second width being wider than the first width.

2. (currently amended): The semiconductor device according to claim 1 including first and second semiconductor devices,

wherein the first semiconductor device and the second semiconductor device are stacked to each other by connecting one end [[s]] of the conductive patterns of each of the devices through a connecting member.

3. (original): The semiconductor device according to claim 1 including first and second semiconductor devices,

wherein the first semiconductor device and the second semiconductor device are stacked by connecting the conductive patterns of the devices through a bar-shaped connecting member.

4. (original): The semiconductor device according to claim 3, wherein a ball-shaped electrode is disposed at a tip end of the bar-shaped member as an external terminal.

5. (original): The semiconductor device according to claim 1, wherein a first terminal electrically connected to the integrated circuit is disposed on a first main surface side of the semiconductor chip, and a second terminal electrically connected to the conductive pattern is disposed on a second main surface side opposite to the first main surface side.

6. (original): The semiconductor device according to claim 5 including first and second semiconductor devices,

wherein the first semiconductor device and the second semiconductor device are stacked by connecting the second terminal of the first semiconductor device to the first terminal of the second semiconductor device.